

## isc Silicon NPN Power Transistor

2SD348

## DESCRIPTION

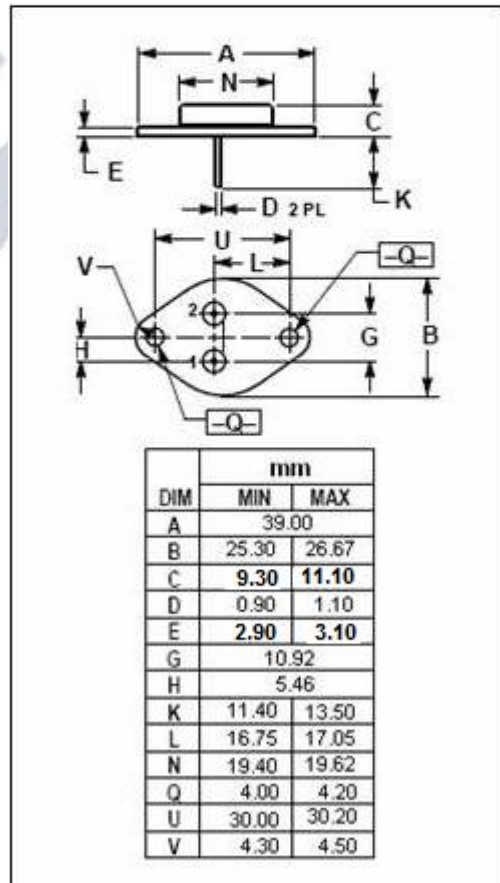
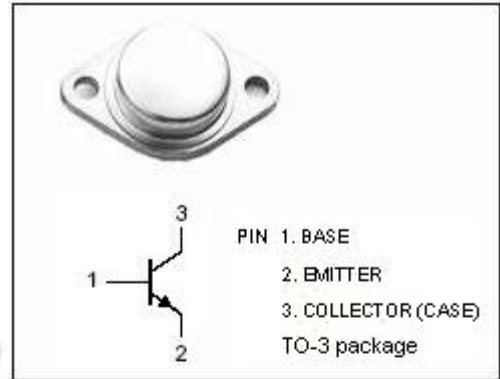
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 400V$  (Min)
- High Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- Designed for use in horizontal deflection circuits of color TV receivers and switching applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current- Continuous	7	A
$I_{CM}$	Collector Current-Peak	12	A
$I_B$	Base Current- Continuous	4	A
$I_{BM}$	Base Current-Peak	6	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	50	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ C$



**isc Silicon NPN Power Transistor****2SD348****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; R <sub>BE</sub> = ∞	400			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	1500			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2.0A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2.0A			1.3	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1500V; I <sub>E</sub> = 0			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			100	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	6		30	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	4.5			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V		6		MHz
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2.0A			1.0	μ s